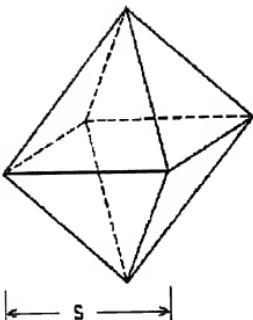


## SEMICONDUCTOR SUBSTRATE

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### Abstract of JP10150048

PROBLEM TO BE SOLVED: To make it hard to generate slit transition from oxygen deposition even under the thermal compression stress, wherein the slit transition can occur, by containing the carbon having a specific concentration in a semiconductor substrate containing oxygen having the specific concentration. SOLUTION: In the substrate containing the oxygen of  $(5\text{--}20)\times 10^{17}$  pieces/cm $^3$ , carbon of  $1\text{--}3.3\times 10^{17}$  pieces/cm $^3$  is contained. At the time of heat treatment in manufacturing an LSI, the many forms of the oxygen deposition is made to be the polyhedron structure. Thus, the slit transition is hard to occur even if thermal stress is loaded, and the LSIs can be manufactured at the high yield.



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